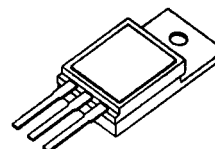




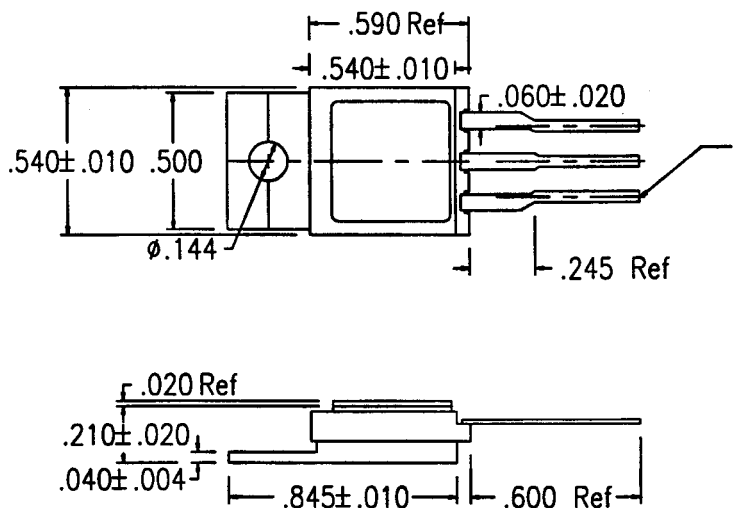
PRELIMINARY

SOLID STATE DEVICES, INC14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**Designer's Data Sheet****FEATURES:**

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed power package
- TX, TXV and Space Level screening available
- Replaces: IRF250 Types

SFF250C
**30 AMP
200 VOLTS
0.085 Ω
N-CHANNEL
POWER MOSFET**
TO-254C**MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	200	Volts
Gate to Source Voltage	V _{GS}	± 20	Volts
Continuous Drain Current	I _D	30	Amps
Operating and Storage Temperature	T _{OP} & T _{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	1	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P _D	125 95	Watts

PACKAGE OUTLINE: CERAMIC TO-254**PIN OUT:**
**PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE**


NOTE: All specifications are subject to change without notification. SSDI's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00053 B**MED**

SFF250C

PRELIMINARY

**SOLID STATE DEVICES, INC**
 14849 Firestone Boulevard · La Mirada, CA 90638
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ELECTRICAL CHARACTERISTICS @ T_J=25°C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250μA)		BVDSS	200	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=60% Rated ID)		RDS(on)	---	0.08	0.085	Ω
On State Drain Current (VDS >ID(on) X RDS(on) Max, VGS=10 V)		ID(on)	30	---	---	A
Gate Threshold Voltage (VDS=VGS, ID=250μA)		VGS(th)	2	3	4	V
Forward Transconductance (VDS >ID(on) X RDS(on) Max, IDS=60% rated ID)		gfs	13	15	---	S(Ω)
Zero Gate Voltage Drain Current (VDS=80% rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125°C)		IDSS	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated VGS	IGSS -	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	VGS=10 Volts 50% rated VDS Rated ID	Qg Qgs Qgd	---	80 12 44	120 20 65	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	VDD=50% rated VDS 50% rated ID RG= 6.2 Ω	td(on) tr td(off) tf	---	20 120 70 80	30 180 100 120	nsec
Diode Forward Voltage (IS=rated ID, VGS=0 V, TJ=25°C)		VSD	---	1.1	2.0	V
Diode Reverse Recovery Time Reverse Recovery Charge	TJ=25°C IF=10A di/dt=100 A/μsec	trr QRR	140 1.8	300 3.8	630 8	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	VGS=0 Volts VDS=25 Volts f= 1 MHz	Ciss Coss Crss	---	2600 650 150	---	pF

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.